

TDA1905

5W AUDIO AMPLIFIER WITH MUTING

DESCRIPTION

The TDA1905 is a monolithic integrated circuit in POWERDIP package, intended for use as low frequency power amplifier in a wide range of applications in radio and TV sets:

- muting facility
- protection against chip over temperature
- very low noise
- high supply voltage rejection
- low "switch-on" noise
- voltage range 4V to 30V

The TDA 1905 is assembled in a new plastic package, the POWERDIP, that offers the same assembly ease, space and cost saving of a normal dual in-line package but with a power dissipation of up to 6W and a thermal resistance of 15° C/W (junction to pins).

ABSOLUTE MAXIMUM RATINGS



Symbol	Parameter	Value	Unit
Vs	Supply voltage	30	V
lo	Output peak current (non repetitive)	3	А
lo	Output peak current (repetitive)	2.5	Α
Vi	Input voltage	0 to + Vs	V
Vi	Differential input voltage	± 7	V
V ₁₁	Muting thresold voltage	Vs	V
P _{tot}	Power dissipation at T _{amb} = 80°C	1	W
	$T_{case} = 60^{\circ}C$	6	W
T _{stg} , T _j	Storage and junction temperature	-40 to 150	°C

APPLICATION CIRCUIT



PIN CONNECTION (top view)



SCHEMATIC DIAGRAM



THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th-j-case}	Thermal resistance junction-pins max	15	°C/W
R _{th-j-amb}	Thermal resistance junction-ambient max	70	°C/W



TEST CIRCUITS:

WITHOUT MUTING



WITH MUTING FUNCTION





ELECTRICAL CHARACTERISTICS (Refer to the test circuit, $T_{amb} = 25$ °C, R_{th} (heatsink) = 20 °C/W, unless otherwisw specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Vs	Supply voltage		4		30	V
Vo	Quiescent output voltage	$V_s = 4V$ $V_s = 14V$ $V_s = 30V$	1.6 6.7 14.4	2.1 7.2 15.5	2.5 7.8 16.8	V
ld	Quiescent drain current	$V_s = 4V$ $V_s = 14V$ $V_s = 30V$		15 17 21	35	mA
V _{CE sat}	Output stage saturation voltage	$I_{C} = 1A$ $I_{C} = 2A$		0.5 1		V
Po	Output power		2.2 5 5 4.5	2.5 5.5 5.5 5.3		W
d	Harmonic distortion			0.1 0.1 0.1 0.1		%
Vi	Input sensitivity	$ \begin{array}{l} f = 1 KHz \\ V_s = 9 V \\ V_s = 14 V \\ V_s = 18 V \\ V_s = 24 V \\ R_L = 4 \Omega \\ R_L = 8 \Omega \\ R_L = 8 \Omega \\ P_o = 5.5 W \\ P_o = 5.3 W \end{array} $		37 49 73 100		mV
Vi	Input saturation voltage (rms)	$V_{s} = 9V$ $V_{s} = 14V$ $V_{s} = 18V$ $V_{s} = 24V$	0.8 1.3 1.8 2.4			V
Ri	Input resistance (pin 8)	f = 1KHz	60	100		KΩ
ld	Drain current	$ \begin{array}{ll} f = 1 KHz & & \\ V_s = 9 V & R_L = 4 \Omega & P_o = 2.5 W \\ V_s = 14 V & R_L = 4 \Omega & P_o = 5.5 W \\ V_s = 18 V & R_L = 8 \Omega & P_o = 5.5 W \\ V_s = 24 V & R_L = 16 \Omega & P_o = 5.3 W \end{array} $		380 550 410 295		mA
η	Efficiency	$ \begin{array}{ll} f = 1 \text{KHz} & & \\ V_{s} = 9 \text{V} & \text{R}_{L} = 4 \Omega & \text{P}_{o} = 2.5 \text{W} \\ V_{s} = 14 \text{V} & \text{R}_{L} = 4 \Omega & \text{P}_{o} = 5.5 \text{W} \\ V_{s} = 18 \text{V} & \text{R}_{L} = 8 \Omega & \text{P}_{o} = 5.5 \text{W} \\ V_{s} = 24 \text{V} & \text{R}_{L} = 16 \Omega & \text{P}_{o} = 5.3 \text{W} \end{array} $		73 71 74 75		%

(*) With an external resistor of 100 Ω between pin 3 and +V_s.



Symbol	Parameter	Te	est conditior	IS	Min.	Тур.	Max.	Unit
BW	Small signal bandwidth (-3dB)	V _s = 14V	$R_L = 4\Omega$	$P_o = 1W$	40 to 40,000			Hz
Gv	Voltage gain (open loop)	V _s = 14V f = 1KHz				75		dB
Gv	Voltage gain (closed loop)	V _s = 14V f = 1KHz	$\begin{array}{l} R_L = 4\Omega \\ P_o = 1W \end{array}$		39.5	40	40.5	dB
е _N	Total input noise		R _g = 50Ω R _g = 1KΩ R _g = 10KΩ	(°)		1.2 1.3 1.5	4.0	μV
			R _g = 50Ω R _g = 1KΩ R _g = 10KΩ	(°°)		2.0 2.0 2.2	6.0	μV
S/N	Signal to noise ratio	$V_s = 14V$ $P_o = 5.5W$	$\begin{array}{l} R_{g} = 10K\Omega\\ R_{g} = 0 \end{array}$	(°)		90 92		dB
		$R_L = 4\Omega$	$R_g = 10K\Omega$ $R_g = 0$	(°°)		87 87		dB
SVR	Supply voltage rejection	V _s = 18V f _{ripple} = 100 V _{ripple} = 0.5	Hz R	g = 10KΩ	40	50		dB
T_{sd}	Thermal shut-down (*) case temperatura		P _{tot} =	2.5W		115		°C

ELECTRICAL CHARACTERISTICS (continued)

MUTING FUNCTION

VT _{OFF}	Muting-off threshold voltage (pin 4)		1.9		4.7	V
VT _{ON} Muting-on threshold voltage (pin 4)			0		1.3	V
			6.2		Vs	
R ₅	Input-resistance (pin 5)	Muting off	80	200		KΩ
		Muting on		10	30	Ω
R4	Input resistance (pin 4)		150			KΩ
AT	Muting attenuation	$R_g + R_1 = 10K\Omega$	50	60		dB

Note: (°) Weighting filter = curve A. (°°) Filter with noise bandwidth: 22 Hz to 22 KHz. (*) See fig. 30 and fig. 31





Figure 2. Quiescent drain current vs. supply voltage 6 - 4777 ldi (mA) 26 20 6 12 6 4 o

¥5 (¥)

Figure 3. Output power vs. supply voltage



Figure 4. Distortion vs. output power ($R_{L} = 16\Omega$)



Figure 5. Distortion vs. output power ($R_{L} = 8\Omega$)

B 12 16 20 74

4



Figure 6. Distortion vs. output power ($R_{L} = 4\Omega$)



Figure 7. Distortion vs. frequency ($R_{L} = 16\Omega$)



Figure 8. Distortion vs. frequency ($R_{\perp} = 8\Omega$)



Figure 9. Distortion vs. frequency ($R_{L} = 4\Omega$)





Figure 10. Open loop frequency response



Figure 11. Output power vs. input voltage



Figure 12. Value of capacitor Cx vs. bandwidth (BW) and gain (Gv)



Figure 13. Supply voltage rejection vs. voltage gain (ref. to the Muting circuit)



Figure 14. Supply voltage reection vs. source resistance



Figure 15. Max power dissipation vs. supply voltage (sine wave operation)



Figure 16. Power dissipation and efficiency vs. output power



Figure 17. Power dissipation and efficiency vs. output power



Figure 18. Power dissipation and efficiency vs. output power





APPLICATION INFORMATION



Figure 19. Application circuit without muting

Figure 20. PC board and components lay-out of the circuit of fig. 19 (1 : 1 scale)



Figure 21. Application circuit with muting



Figure 22. Delayed muting circuit



APPLICATION INFORMATION (continued)

Figure 23. Low-cost application circuit without bootstrap.



Figure 25. Two position DC tone control using change of pin 5 resistance (muting function)



Figure 27. Bass Bomb tone control using change of pin 5 resistance (muting function)







Figure 26. Frequency response of the circuit of fig. 25



Figure 28. Frequency response of the circuit of fig. 27



TDA1905

MUTING FUNCTION

The output signal can be inhibited applying a DC voltage VT to pin 4, as shown in fig. 29

Figure 29



The input resistance at pin 5 depends on the threshold voltage V_T at pin 4 and is typically :

$R_5 = 200 \text{ K}\Omega$	@	$1.9V \le V_T \le 4.7V$	muting-off
$R5 = 10 \Omega$	@	$0V \le VT \le 1.3V$ $6V \le VT \le V_s$	muting-on

Referring to the following input stage, the possible attenuation of the input signal and therefore of the output signal can be found using the following expression:





where R8 \cong 100 $K\Omega$

- during switching at the input stages.

- during the receiver tuning.

The variable impedance capability at pin 5 can be useful in many applications and two examples are shown in fig. 25 and 27, where it has been used to change the feedback network, obtaining 2 different frequency responses.

Considering $R_g = 10 \text{ K}\Omega$ the attenuation in the muting-on condition is typically $A_T = 60 \text{ dB}$. In the muting-off condition, the attenuation is very low, typically 1.2 dB.

Å very low current is necessary to drive the threshold voltage V_T because the input resistance at pin 4 is greater than 150 K Ω . The muting function can be used in many cases, when a temporary inhibition of the output signal is requested, for example:

 in switch-on condition, to avoid preamplifier power-on transients (see fig. 22)



APPLICATION SUGGESTION

The recommended values of the external components are those shown on the application circuit of fig. 21. When the supply voltage V_s is less than 10V, a 100 Ω resistor must be connected between pin 2 and pin 3 in order to obtain the maximum output power. Different values can be used. The following table can help the designer.

Component	Raccom.	Purpose	Larger than	Smaller than	Allowed range	
Component	value	i dipece	recommended value	recommended value	Min.	Max.
R _g + R ₁	10KΩ	Input signal imped. for muting operation	Increase of the attenuation in muting-on condition. Decrease of the input sensitivity.	Decrease of the attenu- ation in muting on condition.		
R ₂	10KΩ	Feedback resistors	Increase of gain.	Decrease of gain. Increase quiescent current.	9 R ₃	
R_3	100Ω		Decrease of gain.	Increase of gain.		1KΩ
R ₄	1ΚΩ	Frequency stability	Danger of oscillation at high frequencies with inductive loads.			
R5	100Ω	Increase of the output swing with low supply voltage.			47	330
P ₁	20ΚΩ	Volume potentiometer	Increase of the switch-on noise.	Decrease of the input impedance and of the input level.	10KΩ	100KΩ
$egin{array}{cc} C_1 \ C_2 \ C_3 \end{array}$	0.22µF	Input DC decoupling.	Higher cost lower noise.	Higher low frequency cutoff. Higher noise.		
C ₄	2.2µF	Inverting input DC decoupling.	Increase of the switch- on noise.	Higher low frequency cutoff.	0.1µF	
C ₅	0.1µF	Supply voltage bypass.		Danger of oscillations.		
C ₆	10µF	Ripple rejection	Increase of SVR increase of the switch-on time	Degradation of SVR	2.2µF	100μF
C7	47μF	Bootstrap.		Increase of the distortion at low frequency.	10µF	100μF
C ₈	0.22µF	Frequency stability.		Danger of oscillation.		
C ₉	1000µF	Output DC decoupling.		Higher low frequency cutoff.		



THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- 1) An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily tolerated since the Tj cannot be higher than 150 °C.
- 2) The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature. If for any reason, the junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation and the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 32 shows this dissipable power as a function of ambient temperature for different thermal resistance.



MOUNTING INSTRUCTION : See TDA1904



DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.85		1.40	0.033		0.055	
b		0.50			0.020		
b1	0.38		0.50	0.015		0.020	
D			20.0			0.787	
E		8.80			0.346		
e		2.54			0.100		
e3		17.78			0.700		
F			7.10			0.280	
I			5.10			0.201	
L		3.30			0.130		
Z			1.27			0.050	

POWERDIP PACKAGE MECHANICAL DATA



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thaliand - United Kingdom - U.S.A.

